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(71) Applicant: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: MARXSEN, Gerd, Franz; Wettinstr. 10, 01445 Radebeul (DE). PREUSSE, Axel; Humboldtstr. 3, 01445 Radebeul (DE). NOPPER, Markus; Virchowstrasse 31, 01129 Dresden (DE). MAUERSBERGER, Frank; HoflossnitzStr. 2e, 01445 Radebeul (DE).

(74) Agent: DRAKE, Paul, E.; Advanced Micro Devices, Inc., 5204 East Ben White Boulevard, Mail Stop 562, Austin, TX 78741 (US).

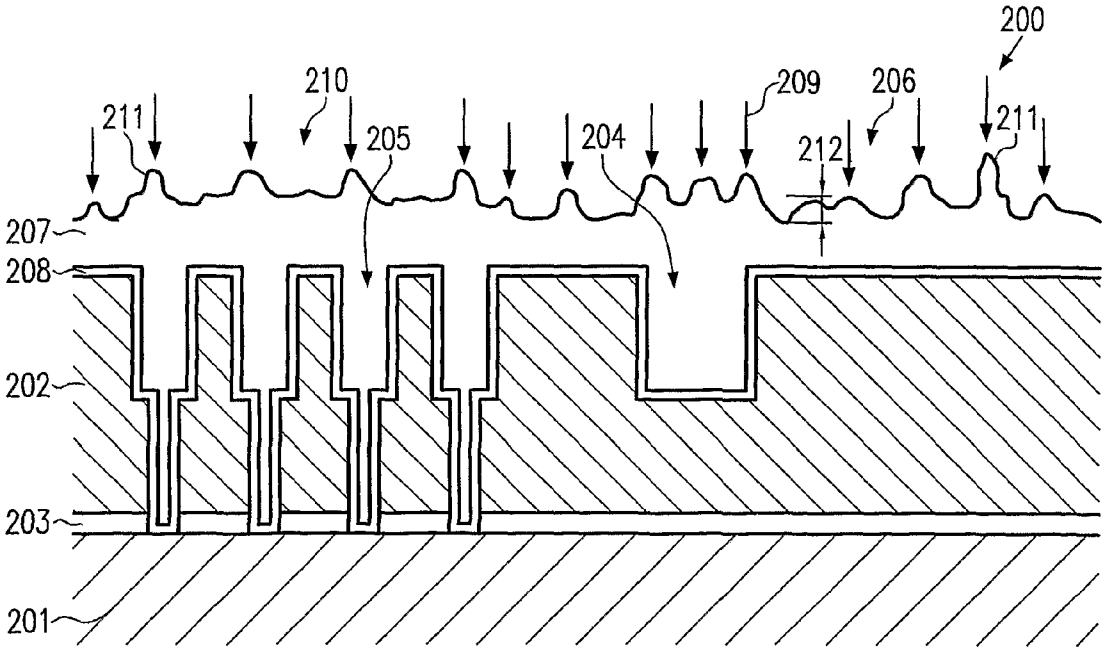
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(54) Title: METHOD OF ELECTROPLATING COPPER OVER A PATTERNED DIELECTRIC LAYER TO ENHANCE PROCESS UNIFORMITY OF A SUBSEQUENT CMP PROCESS



(57) Abstract: In a new method of plating metal onto dielectric layers including small diameter vias and large diameter trenches 205, a surface roughness is created by e.g. reducing the amount of leveler in the plating bath at least on non-patterned regions 206 of the dielectric layer 203 to enhance the uniformity of material removal in a subsequent chemical mechanical polishing (CMP) process.

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